

Final datasheet

XHP™2 module with Trench/Fieldstop IGBT5, emitter controlled 5 diode and NTC

Features

- Electrical features
 - $V_{CES} = 1700\text{ V}$
 - $I_{C\text{ nom}} = 1200\text{ A} / I_{CRM} = 2400\text{ A}$
 - Extended operating temperature $T_{vj\text{ op}}$
 - High current density
 - Low switching losses
 - Low $V_{CE,sat}$
 - $T_{vj,op} = 175^{\circ}\text{C}$
- Mechanical features
 - High creepage and clearance distances
 - High power and thermal cycling capability
 - High power density
 - Package with CTI > 600



Potential applications

- High-power converters
- Motor drives
- Traction drives
- Wind turbines

Product validation

- Qualified for industrial applications according to the relevant tests of IEC 60747, 60749 and 60068

Description

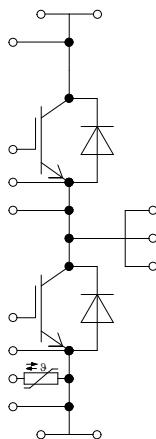


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1 Package

Table 1 Insulation coordination

Parameter	Symbol	Note or test condition	Values	Unit
Isolation test voltage	V_{ISOL}	RMS, $f = 50$ Hz	4.0	kV
Material of module baseplate			Cu	
Creepage distance	d_{Creep}	terminal to heatsink	40.0	mm
Creepage distance	d_{Creep}	terminal to terminal	34.0	mm
Clearance	d_{Clear}	terminal to heatsink	31.0	mm
Clearance	d_{Clear}	terminal to terminal	8.0	mm
Comparative tracking index	CTI		> 600	

Table 2 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Stray inductance module	L_{sCE}			10		nH
Module lead resistance, terminals - chip	$R_{AA'+CC'}$	$T_C = 25$ °C, per switch		0.3		mΩ
Module lead resistance, terminals - chip	$R_{CC'+EE'}$	$T_C = 25$ °C, per switch		0.35		mΩ
Storage temperature	T_{stg}		-40		150	°C
Maximum baseplate operation temperature	T_{BPmax}				150	°C
Mounting torque for module mounting	M	- Mounting according to valid application note	M6, Screw	3	6	Nm
Terminal connection torque	M	- Mounting according to valid application note	M3, Screw	0.9	1.1	Nm
			M8, Screw	8	10	
Weight	G			1020		g

2 IGBT, Inverter

Table 3 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit
Collector-emitter voltage	V_{CES}	$T_{vj} = 25$ °C	1700	V
Implemented collector current	I_{CN}		1200	A
Continuous DC collector current	I_{CDC}	$T_{vj\ max} = 175$ °C $T_C = 75$ °C	1200	A

(table continues...)

Table 3 (continued) Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit
Repetitive peak collector current	I_{CRM}	t_p limited by $T_{vj\ op}$	2400	A
Gate-emitter peak voltage	V_{GES}		±20	V

Table 4 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Collector-emitter saturation voltage	$V_{CE\ sat}$	$I_C = 1200\ A, V_{GE} = 15\ V$	$T_{vj} = 25\ ^\circ C$	1.80	2.25	V
			$T_{vj} = 125\ ^\circ C$	2.20	2.75	
			$T_{vj} = 175\ ^\circ C$	2.40	3.00	
Gate threshold voltage	V_{GEth}	$I_C = 43\ mA, V_{CE} = V_{GE}, T_{vj} = 25\ ^\circ C$	5.35	5.80	6.25	V
Gate charge	Q_G	$V_{GE} = \pm 15\ V, V_{CC} = 900\ V$		5.5		μC
Internal gate resistor	R_{Gint}	$T_{vj} = 25\ ^\circ C$		0.75		Ω
Input capacitance	C_{ies}	$f = 100\ kHz, T_{vj} = 25\ ^\circ C, V_{CE} = 25\ V, V_{GE} = 0\ V$		56		nF
Reverse transfer capacitance	C_{res}	$f = 100\ kHz, T_{vj} = 25\ ^\circ C, V_{CE} = 25\ V, V_{GE} = 0\ V$		2		nF
Collector-emitter cut-off current	I_{CES}	$V_{CE} = 1700\ V, V_{GE} = 0\ V$			10	mA
Gate-emitter leakage current	I_{GES}	$V_{CE} = 0\ V, V_{GE} = 20\ V, T_{vj} = 25\ ^\circ C$			400	nA
Turn-on delay time (inductive load)	t_{don}	$I_C = 1200\ A, V_{CC} = 900\ V, V_{GE} = \pm 15\ V, R_{Gon} = 0.5\ \Omega$	$T_{vj} = 25\ ^\circ C$	0.173		μs
			$T_{vj} = 125\ ^\circ C$	0.180		
			$T_{vj} = 175\ ^\circ C$	0.183		
Rise time (inductive load)	t_r	$I_C = 1200\ A, V_{CC} = 900\ V, V_{GE} = \pm 15\ V, R_{Gon} = 0.5\ \Omega$	$T_{vj} = 25\ ^\circ C$	0.090		μs
			$T_{vj} = 125\ ^\circ C$	0.095		
			$T_{vj} = 175\ ^\circ C$	0.105		
Turn-off delay time (inductive load)	t_{doff}	$I_C = 1200\ A, V_{CC} = 900\ V, V_{GE} = \pm 15\ V, R_{Goff} = 4.5\ \Omega$	$T_{vj} = 25\ ^\circ C$	1.050		μs
			$T_{vj} = 125\ ^\circ C$	1.150		
			$T_{vj} = 175\ ^\circ C$	1.210		
Fall time (inductive load)	t_f	$I_C = 1200\ A, V_{CC} = 900\ V, V_{GE} = \pm 15\ V, R_{Goff} = 4.5\ \Omega$	$T_{vj} = 25\ ^\circ C$	0.180		μs
			$T_{vj} = 125\ ^\circ C$	0.410		
			$T_{vj} = 175\ ^\circ C$	0.560		
Turn-on energy loss per pulse	E_{on}	$I_C = 1200\ A, V_{CC} = 900\ V, L_\sigma = 20\ nH, V_{GE} = \pm 15\ V, R_{Gon} = 0.5\ \Omega, di/dt = 12700\ A/\mu s (T_{vj} = 175\ ^\circ C)$	$T_{vj} = 25\ ^\circ C$	220		mJ
			$T_{vj} = 125\ ^\circ C$	340		
			$T_{vj} = 175\ ^\circ C$	420		

(table continues...)

Table 4 (continued) **Characteristic values**

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Turn-off energy loss per pulse	E_{off}	$I_C = 1200\text{ A}$, $V_{CC} = 900\text{ V}$, $L_\sigma = 20\text{ nH}$, $V_{GE} = \pm 15\text{ V}$, $R_{Goff} = 4.5\ \Omega$, $dv/dt = 1800\text{ V}/\mu\text{s}$ ($T_{vj} = 175\text{ °C}$)	$T_{vj} = 25\text{ °C}$	355		mJ
			$T_{vj} = 125\text{ °C}$	465		
			$T_{vj} = 175\text{ °C}$	535		
SC data	I_{SC}	$V_{GE} \leq 15\text{ V}$, $V_{CC} = 1000\text{ V}$, $V_{CEmax} = V_{CES} - L_{sCE} \cdot di/dt$	$t_p \leq 10\ \mu\text{s}$, $T_{vj} = 175\text{ °C}$	4600		A
Thermal resistance, junction to case	R_{thJC}	per IGBT			26.8	K/kW
Thermal resistance, case to heat sink	R_{thCH}	per IGBT, $\lambda_{grease} = 1\text{ W}/(\text{m}\cdot\text{K})$		20.1		K/kW
Temperature under switching conditions	T_{vjop}		-40		175	°C

3 Diode, Inverter

Table 5 **Maximum rated values**

Parameter	Symbol	Note or test condition	Values	Unit	
Repetitive peak reverse voltage	V_{RRM}	$T_{vj} = 25\text{ °C}$	1700	V	
Continuous DC forward current	I_F		1200	A	
Repetitive peak forward current	I_{FRM}	$t_p = 1\text{ ms}$	2400	A	
I^2t - value	I^2t	$t_p = 10\text{ ms}$, $V_R = 0\text{ V}$	$T_{vj} = 125\text{ °C}$	338	kA ² s
			$T_{vj} = 175\text{ °C}$	276	
Maximum power dissipation	P_{RQM}	$T_{vj} = 175\text{ °C}$	1200	kW	

Table 6 **Characteristic values**

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Forward voltage	V_F	$I_F = 1200\text{ A}$, $V_{GE} = 0\text{ V}$	$T_{vj} = 25\text{ °C}$	1.75	2.10	V
			$T_{vj} = 125\text{ °C}$	1.70	2.05	
			$T_{vj} = 175\text{ °C}$	1.70	2.05	
Peak reverse recovery current	I_{RM}	$V_{CC} = 900\text{ V}$, $I_F = 1200\text{ A}$, $V_{GE} = -15\text{ V}$, $-di_F/dt = 12700\text{ A}/\mu\text{s}$ ($T_{vj} = 175\text{ °C}$)	$T_{vj} = 25\text{ °C}$	1300		A
			$T_{vj} = 125\text{ °C}$	1500		
			$T_{vj} = 175\text{ °C}$	1600		

(table continues...)

Table 6 (continued) **Characteristic values**

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Recovered charge	Q_r	$V_{CC} = 900\text{ V}$, $I_F = 1200\text{ A}$, $V_{GE} = -15\text{ V}$, $-di_F/dt =$ $12700\text{ A}/\mu\text{s}$ ($T_{vj} = 175\text{ °C}$)	$T_{vj} = 25\text{ °C}$	240		μC
			$T_{vj} = 125\text{ °C}$	455		
			$T_{vj} = 175\text{ °C}$	585		
Reverse recovery energy	E_{rec}	$V_{CC} = 900\text{ V}$, $I_F = 1200\text{ A}$, $V_{GE} = -15\text{ V}$, $-di_F/dt =$ $12700\text{ A}/\mu\text{s}$ ($T_{vj} = 175\text{ °C}$)	$T_{vj} = 25\text{ °C}$	150		mJ
			$T_{vj} = 125\text{ °C}$	290		
			$T_{vj} = 175\text{ °C}$	365		
Thermal resistance, junction to case	R_{thJC}	per diode			51.4	K/kW
Thermal resistance, case to heat sink	R_{thCH}	per diode, $\lambda_{grease} = 1\text{ W}/(\text{m}\cdot\text{K})$		27.1		K/kW
Temperature under switching conditions	$T_{vj\text{ op}}$		-40		175	$^{\circ}\text{C}$

4 NTC-Thermistor

Table 7 **Characteristic values**

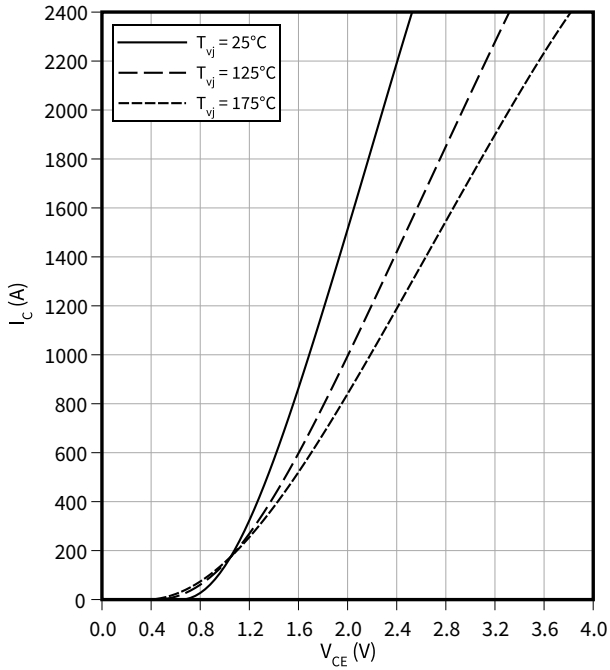
Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Rated resistance	R_{25}	$T_{NTC} = 25\text{ °C}$		5		k Ω
Deviation of R_{100}	$\Delta R/R$	$T_{NTC} = 100\text{ °C}$, $R_{100} = 493\text{ }\Omega$	-5		5	%
Power dissipation	P_{25}	$T_{NTC} = 25\text{ °C}$			20	mW
B-value	$B_{25/50}$	$R_2 = R_{25} \exp[B_{25/50}(1/T_2 - 1/(298,15\text{ K}))]$		3375		K
B-value	$B_{25/80}$	$R_2 = R_{25} \exp[B_{25/80}(1/T_2 - 1/(298,15\text{ K}))]$		3411		K
B-value	$B_{25/100}$	$R_2 = R_{25} \exp[B_{25/100}(1/T_2 - 1/(298,15\text{ K}))]$		3433		K

Note: For an analytical description of the NTC characteristics please refer to AN2009-10, chapter 4

5 Characteristics diagrams

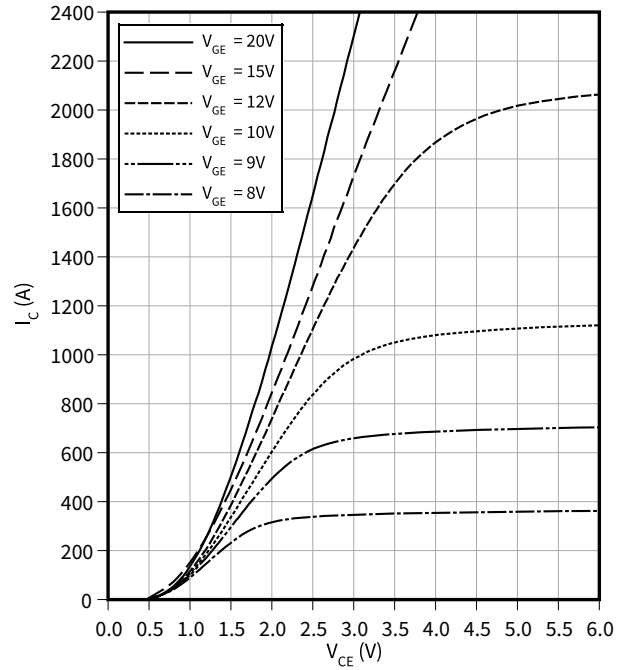
Output characteristic (typical), IGBT, Inverter

$I_C = f(V_{CE})$
 $V_{GE} = 15\text{ V}$



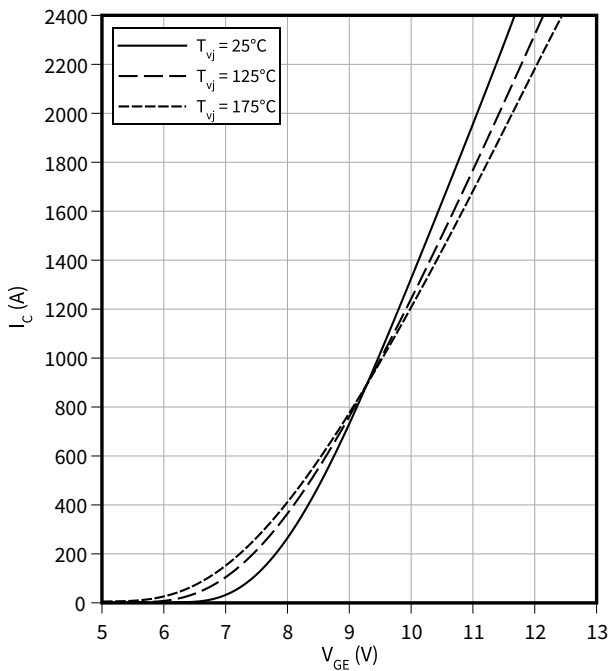
Output characteristic field (typical), IGBT, Inverter

$I_C = f(V_{CE})$
 $T_{vj} = 175\text{ °C}$



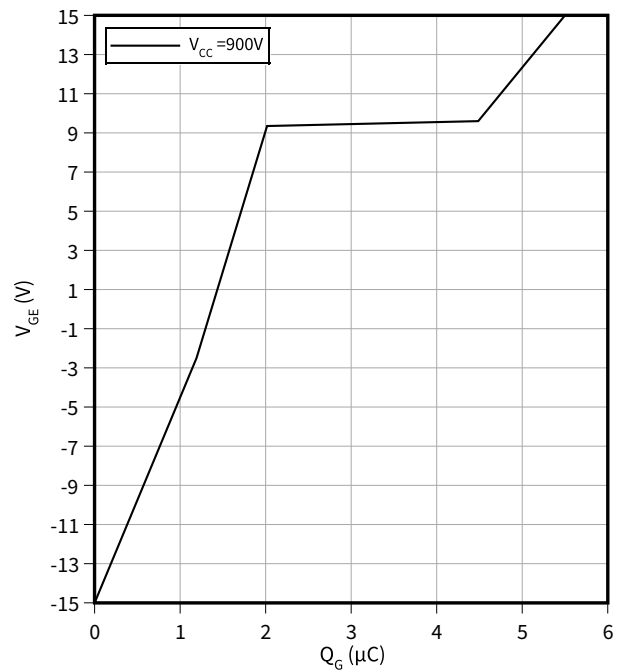
Transfer characteristic (typical), IGBT, Inverter

$I_C = f(V_{GE})$
 $V_{CE} = 20\text{ V}$



Gate charge characteristic (typical), IGBT, Inverter

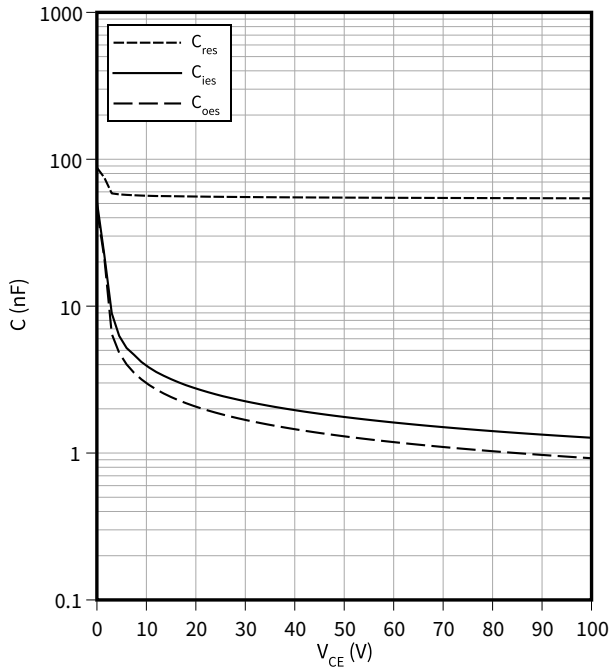
$V_{GE} = f(Q_G)$
 $I_C = 1200\text{ A}, T_{vj} = 25\text{ °C}$



5 Characteristics diagrams

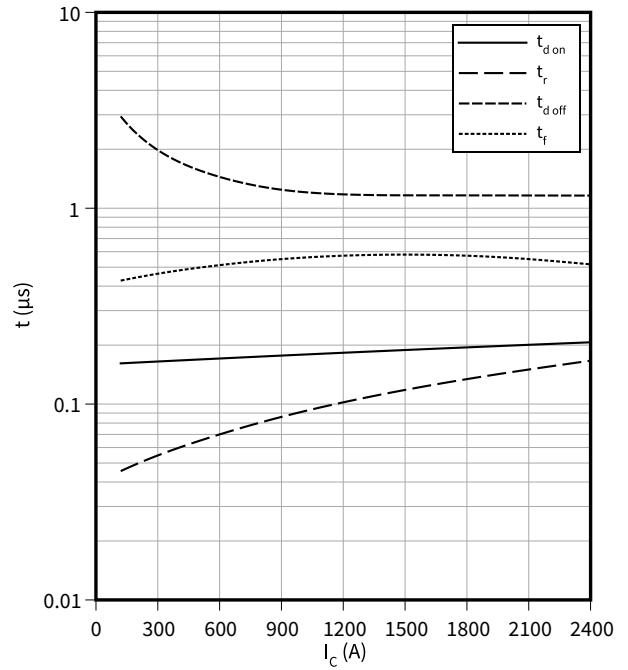
Capacity characteristic (typical), IGBT, Inverter

$C = f(V_{CE})$
 $f = 100 \text{ kHz}, V_{GE} = 0 \text{ V}, T_{vj} = 25 \text{ }^\circ\text{C}$



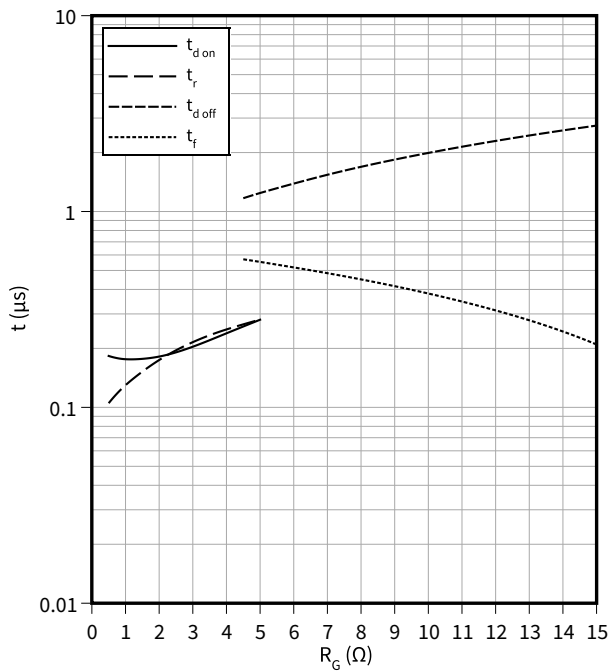
Switching times (typical), IGBT, Inverter

$t = f(I_C)$
 $R_{Goff} = 4.5 \text{ } \Omega, R_{Gon} = 0.5 \text{ } \Omega, V_{GE} = \pm 15 \text{ V}, V_{CC} = 900 \text{ V}, T_{vj} = 175 \text{ }^\circ\text{C}$



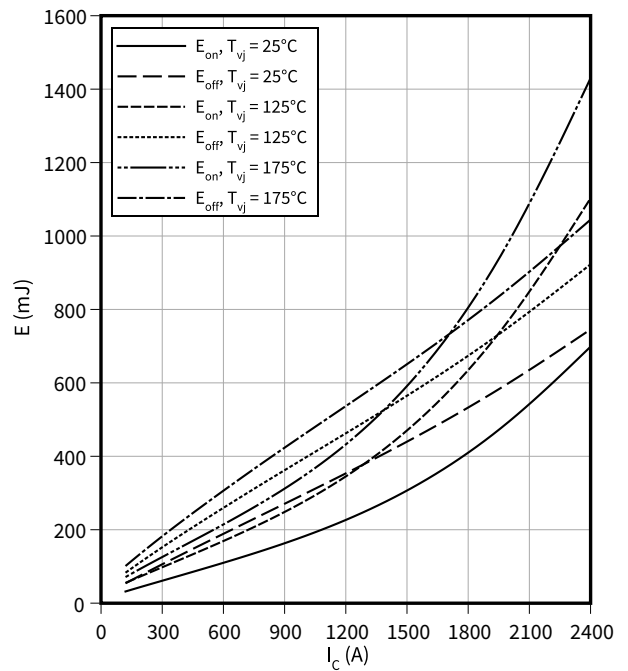
Switching times (typical), IGBT, Inverter

$t = f(R_G)$
 $V_{GE} = \pm 15 \text{ V}, I_C = 1200 \text{ A}, V_{CC} = 900 \text{ V}, T_{vj} = 175 \text{ }^\circ\text{C}$



Switching losses (typical), IGBT, Inverter

$E = f(I_C)$
 $R_{Goff} = 4.5 \text{ } \Omega, R_{Gon} = 0.5 \text{ } \Omega, V_{CC} = 900 \text{ V}, V_{GE} = \pm 15 \text{ V}$

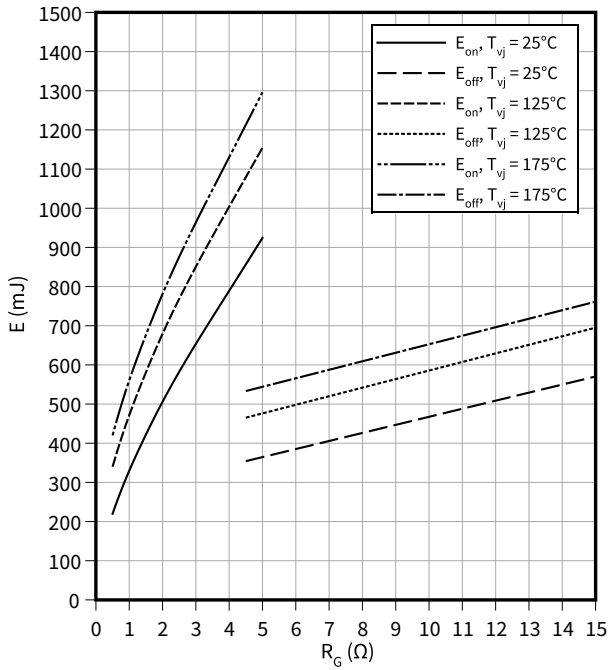


5 Characteristics diagrams

Switching losses (typical), IGBT, Inverter

$E = f(R_G)$

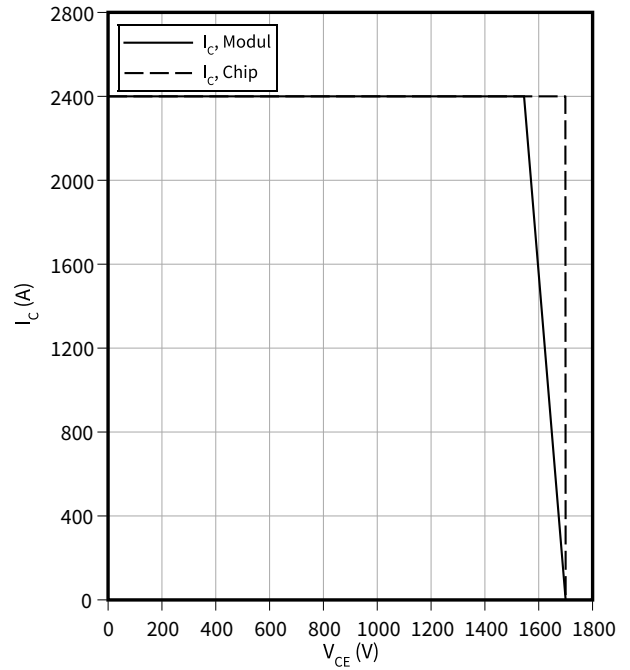
$I_C = 1200 \text{ A}, V_{CC} = 900 \text{ V}, V_{GE} = \pm 15 \text{ V}$



Reverse bias safe operating area (RBSOA), IGBT, Inverter

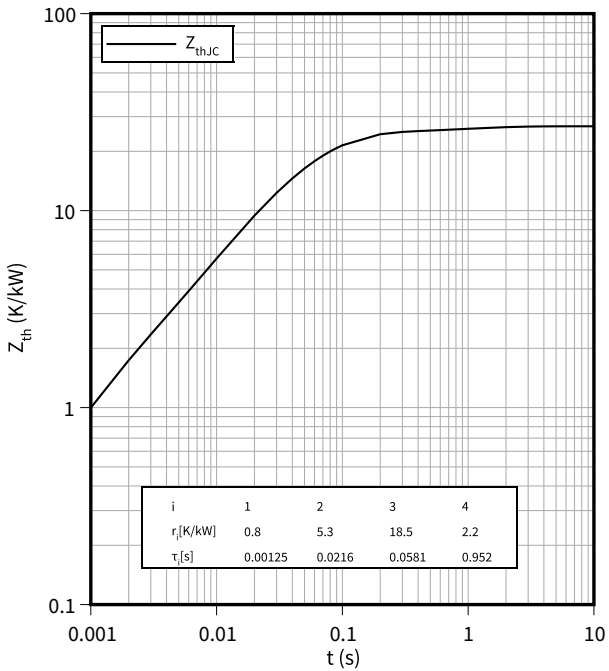
$I_C = f(V_{CE})$

$R_{Goff} \geq 4.5 \Omega, V_{GE} = \pm 15 \text{ V}, T_{vj} = 175 \text{ °C}$



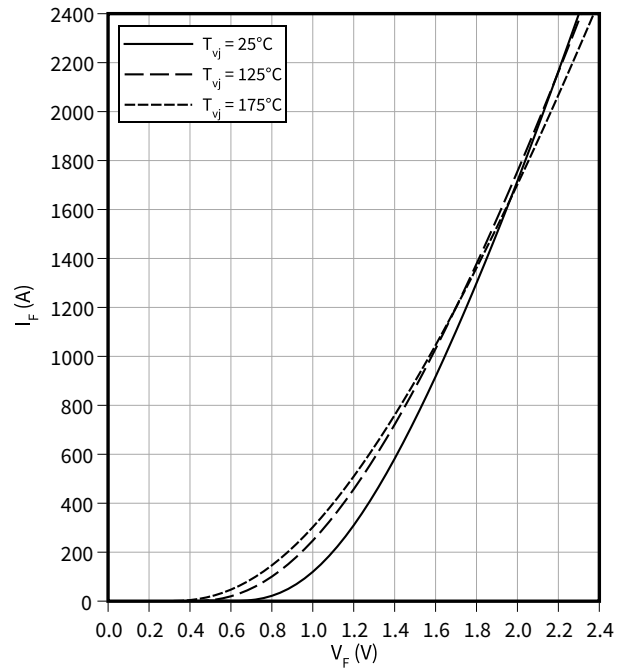
Transient thermal impedance, IGBT, Inverter

$Z_{th} = f(t)$



Forward characteristic (typical), Diode, Inverter

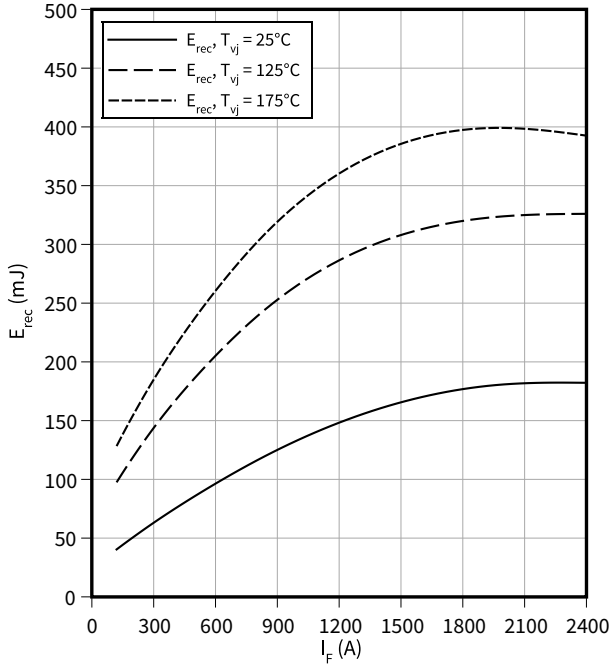
$I_F = f(V_F)$



5 Characteristics diagrams

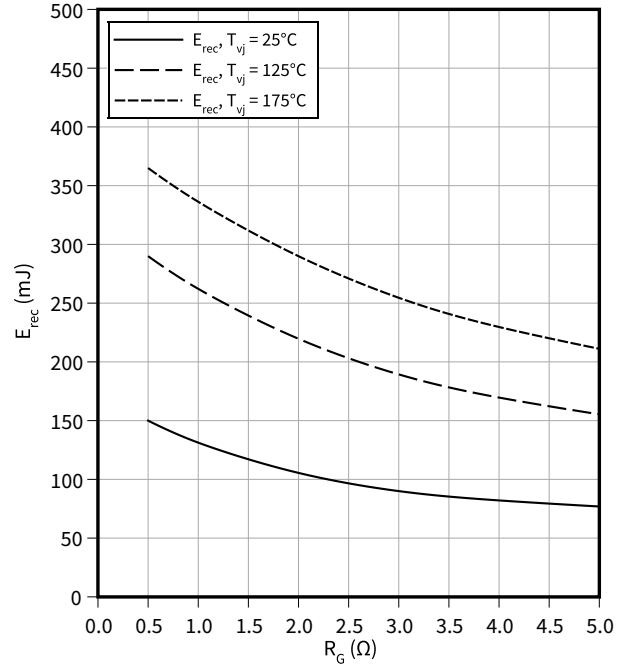
Switching losses (typical), Diode, Inverter

$E_{rec} = f(I_F)$
 $V_{CE} = 900\text{ V}$, $R_{Gon} = R_{Gon}(IGBT)$



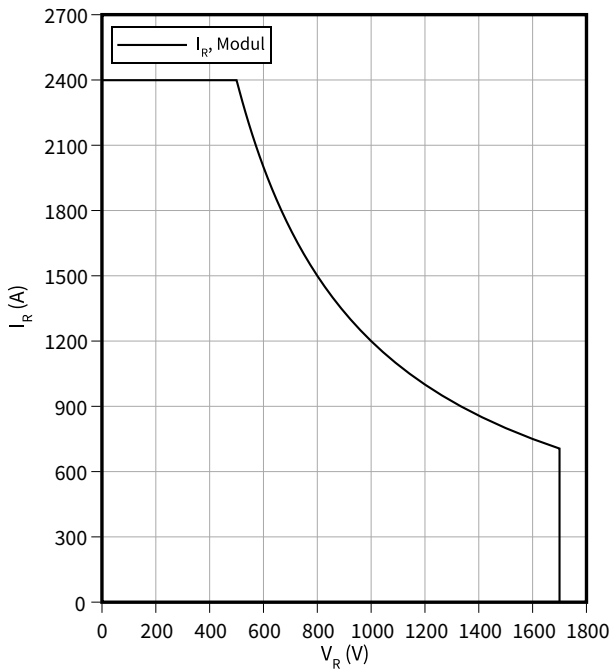
Switching losses (typical), Diode, Inverter

$E_{rec} = f(R_G)$
 $V_{CE} = 900\text{ V}$, $I_F = 1200\text{ A}$



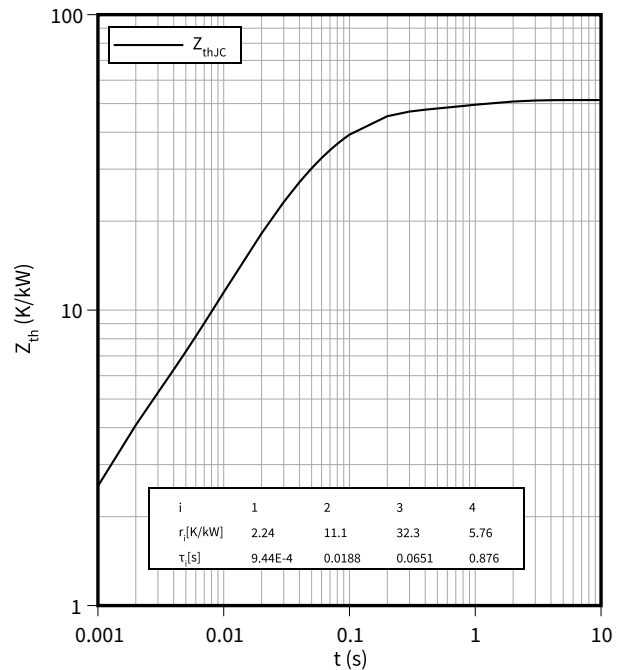
Safe operating area (SOA), Diode, Inverter

$I_R = f(V_R)$
 $T_{vj} = 175^\circ\text{C}$



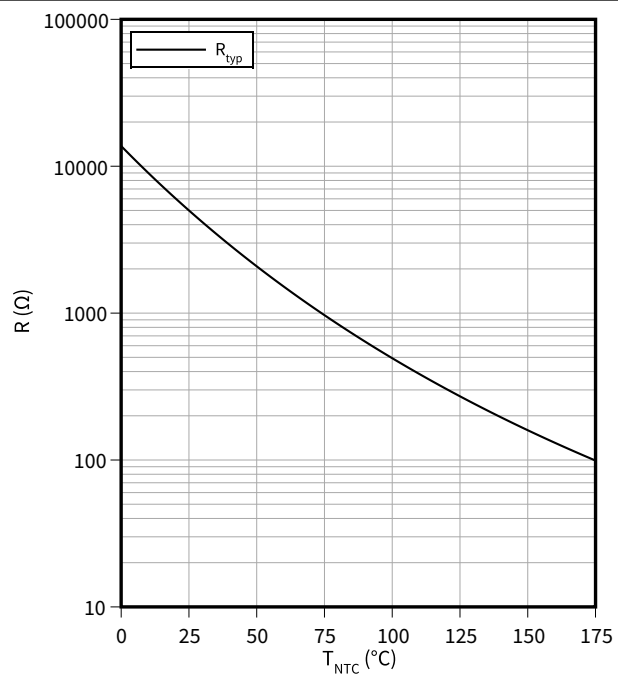
Transient thermal impedance, Diode, Inverter

$Z_{th} = f(t)$



Temperature characteristic (typical), NTC-Thermistor

$R = f(T_{NTC})$



6 Circuit diagram

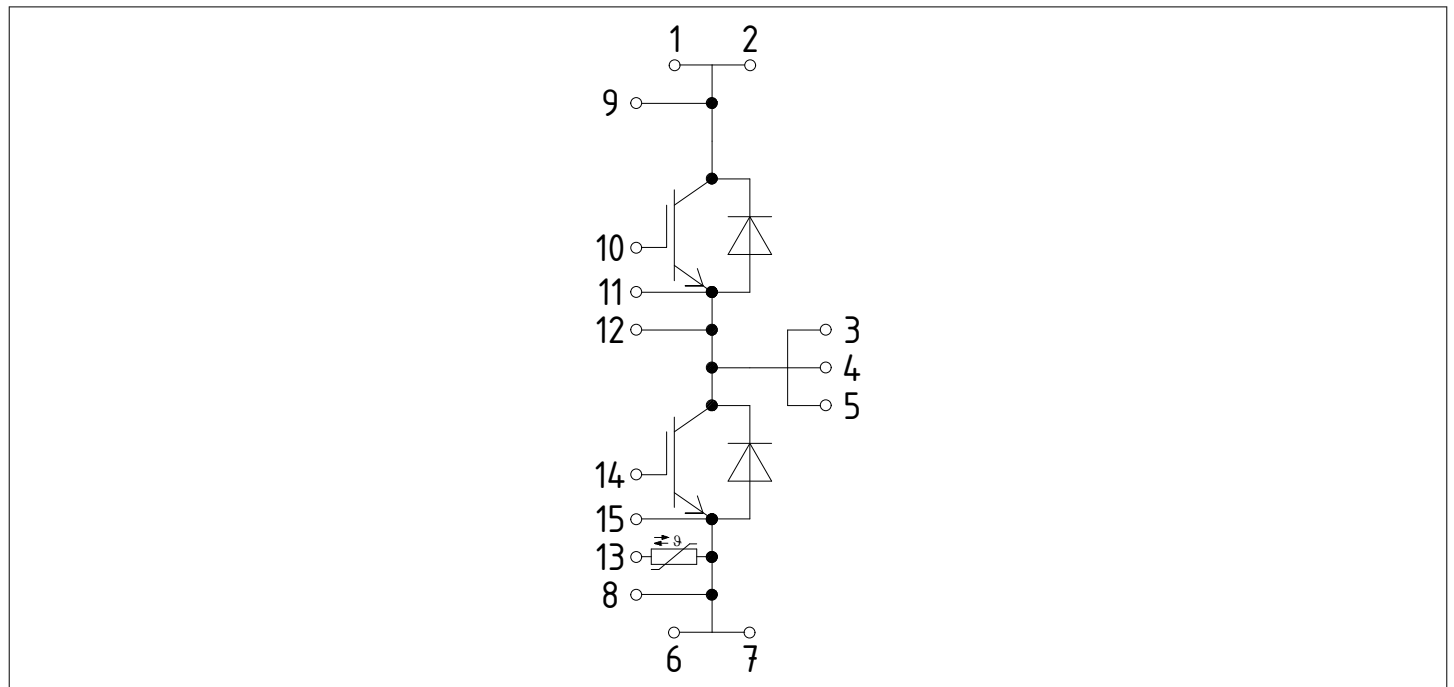


Figure 1

7 Package outlines

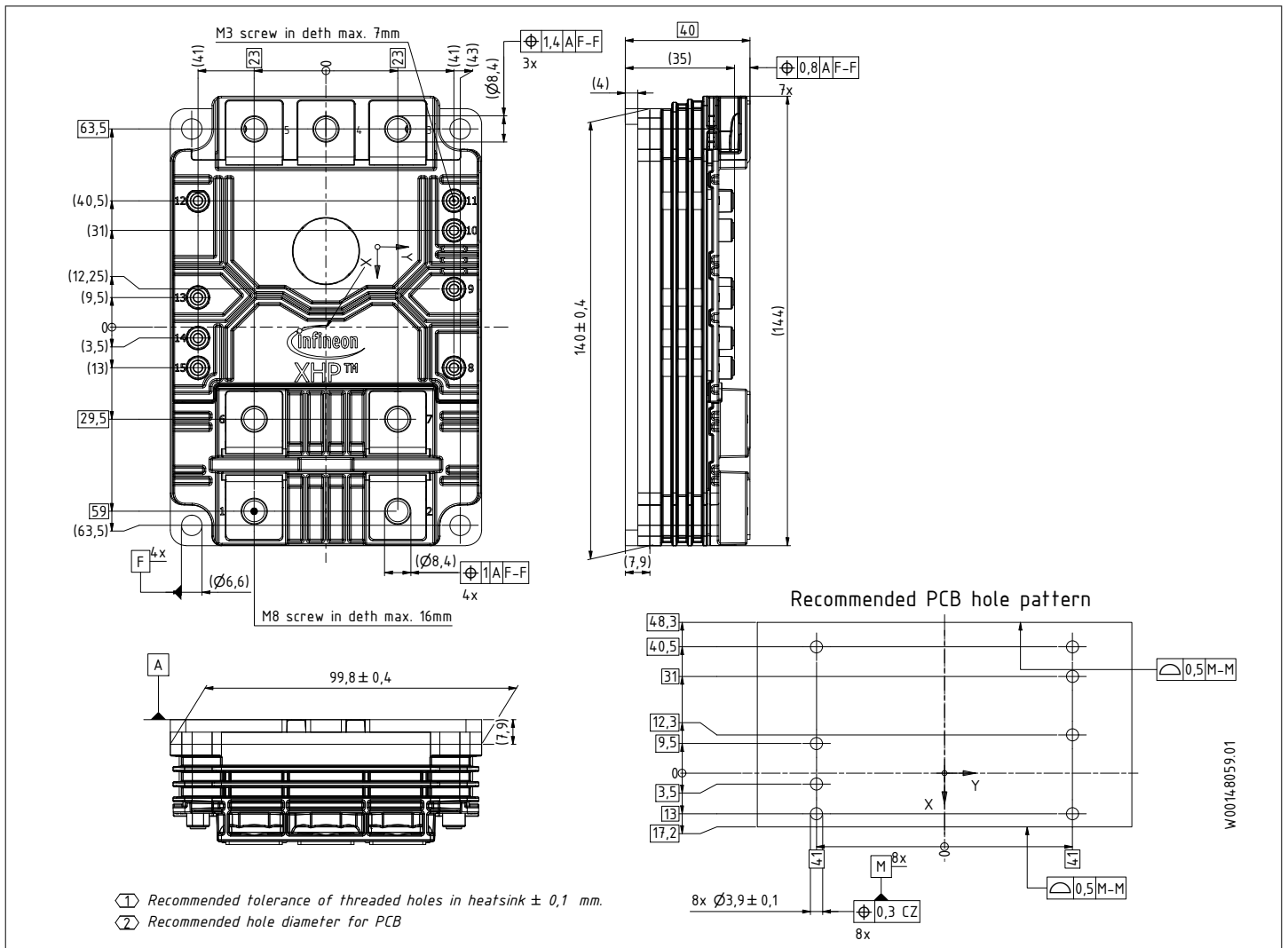


Figure 2

8 Module label code


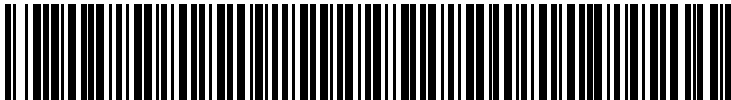
Module label code			
Code format	Data Matrix	Barcode Code128	
Encoding	ASCII text	Code Set A	
Symbol size	16x16	23 digits	
Standard	IEC24720 and IEC16022	IEC8859-1	
Code content	<i>Content</i> Module serial number Module material number Production order number Date code (production year) Date code (production week)	<i>Digit</i> 1 - 5 6 - 11 12 - 19 20 - 21 22 - 23	<i>Example</i> 71549 142846 55054991 15 30
Example	 		
	71549142846550549911530		71549142846550549911530

Figure 3

Revision history

Document revision	Date of release	Description of changes
V1.0	2019-02-06	Target datasheet
V1.1	2020-04-02	Target datasheet
n/a	2020-09-01	Datasheet migrated to a new system with a new layout and new revision number schema: target or preliminary datasheet = 0.xy; final datasheet = 1.xy
0.10	2021-05-04	Target datasheet
0.20	2022-11-03	Preliminary datasheet
1.00	2023-10-30	Final datasheet

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Edition 2023-10-30

Published by

Infineon Technologies AG

81726 Munich, Germany

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IFX-AA150-005

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